AZ P4330-RS — run sheet

Merck KGaA (AZ Electronic Materials)

nanyte.com/photoresists/az-p4330-rs · last updated 2026-09-28

Thickness: 3–5 µm

Softbake: 95–115 °C

Rehydrate: 30–60 min (films over 4 µm, 40–45 % RH)

Exposure dose — dose by film thickness · Suss MA-200 mask aligner

Film thickness	Dose
1.5 µm	90 mJ/cm²
3.5 µm	135 mJ/cm²
12 µm	800 mJ/cm²

Develop: Developer AZ 400K at 1:4, or at 1:3 / AZ 421K (unbuffered) for films above 12 µm; AZ Developer 1:1 where aluminium must not be etched; AZ 340 is also listed · Dilution AZ 400K 1:4 for better selectivity on thinner films, 1:3 for films above 12 µm; AZ Developer 1:1 · Method spray or immersion

Hardbake: 100–110 °C